Vladimir N Poroshin

List of Publications by Year
in descending order

34 papers	235 citations	1040056 9 h-index	996975 15 g-index
34 all docs	34 docs citations	34 times ranked	244 citing authors

#	Article	IF	Citations
1	Dependence of Meyerâ€“Neldel energy on energetic disorder in organic field effect transistors. Applied Physics Letters, 2010, 96, 213306.	3.3	41
2	Multifunctionality of lanthanumâ€“strontium manganite nanopowder. Physical Chemistry Chemical Physics, 2020, 22, 11817-11828.	2.8	28
3	Tin induced a-Si crystallization in thin films of Si-Sn alloys. Journal of Applied Physics, 2013, 114, .	2.5	26
4	Interaction of surface plasmon polaritons in heavily doped GaN microstructures with terahertz radiation. Journal of Applied Physics, 2016, 119, .	2.5	22
5	Measurement of the transient heat transfer to liquid helium from a thin metal film. Cryogenics, 1983, 23, 546-548.	1.7	11
6	Specific interactions and charge transport in ternary PVDF/polyaniline/MWCNT nanocomposite films. Composites Science and Technology, 2020, 198, 108284.	7.8	11
7	On the possibility of tuning the energy separation between space-quantized levels in a quantum well. Philosophical Magazine Letters, 2013, 93, 42-49.	1.2	10
8	On some new effects in delta-doped QWs. Physica E: Low-Dimensional Systems and Nanostructures, 2015, 66, 162-169.	2.7	10
9	Limit of transient heat absorption by superfluid helium for very large heat pulses. Cryogenics, 1989, 29, 444-447.	1.7	9
10	Lateral transport and far-infrared radiation of electrons in In x Ga1 â^' x As/GaAs heterostructures with the double tunnel-coupled quantum wells in a high electric field. Semiconductors, 2010, 44, 1495-1498.	0.5	9
11	Transport properties of InGaAs/GaAs Heterostructures with Î´-doped quantum wells. Semiconductors, 2012, 46, 631-636.	0.5	9
12	Does the Temperature Dependence of the Charge Carrier Mobility in Disordered Organic Semiconductors at Large Carrier Concentrations Obey the Meyerâ€“Neldel Compensation Law?. Molecular Crystals and Liquid Crystals, 2011, 535, 1-9.	0.9	5
13	Influence of conduction via a channel of an impurity Î´-layer on the magneto-quantum effects in AlGaAs/GaAs/AlGaAs heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 60, 31-36.	2.7	5
14	Investigation of Nonequilibrium Phonons in GaAs. Physica Status Solidi (B): Basic Research, 1986, 136, 63-68.	1.5	4
15	Nature of damped current oscillations in the formation of a static acoustoelectric domain in a n-InGaAs/GaAs quantum-well heterostructure. Semiconductors, 2008, 42, 589-592.	0.5	4
16	Interband and intraband radiation from the n-InGaAs/GaAs heterostructures with quantum wells under the conditions of injection in high lateral electric fields. Physica E: Low-Dimensional Systems and Nanostructures, 2015, 74, 328-333.	2.7	4
17	Electron and photon emission from discontinuous carbon films. International Journal of Electronics, 1992, 73, 1005-1008.	1.4	3
18	Long-term photoconductivity decay in n-InGaAs/GaAs heterostructures with coupled quantum wells under band-to-band excitation. Semiconductors, 2013, 47, 174-177.	0.5	3

#	Article	IF	Citations
19	A peculiarity of quantum hot-electron real space transfer in dual-channel GaAs-based heterostructures. Journal of Physics Communications, 2017, 1, 045002.	1.2	3
20	Effect of barrier width between GaAs/InGaAs/GaAs double coupled quantum wells on bipolar transport and terahertz radiation by hot carriers in lateral electric field. Low Temperature Physics, 2020, 46, 633-638.	0.6	3
21	Self-induced birefringence of infrared light inn-Ge. Physical Review Letters, 1993, 71, 3027-3030.	7.8	2
22	Far-infrared radiation from n-InGaAs/GaAs quantum-well heterostructures in high lateral electric fields under injection conditions. Semiconductors, 2014, 48, 625-629.	0.5	2
23	Magnetoresistance of composite carbon sensors in strong electric fields in the liquid helium temperature range. Low Temperature Physics, 2017, 43, 367-370.	0.6	2
24	Electric transport properties in the 2D-MoS₂. Molecular Crystals and Liquid Crystals, 2022, 749, 87-92.	0.9	2
25	Infrared light scattering by free holes in p-Ge. Semiconductor Science and Technology, 1994, 9, 1790-1794.	2.0	1
26	<title>Screened Coulomb potential approach for the study of resonant impurity states in uniaxially deformed p-Ge</title>. , 2001, , .		1
27	Energy characteristics of boron impurity in Siâˆ•Si1âˆ’xGex heterostructures with on-center and on-edge selective doping of quantum wells. Low Temperature Physics, 2007, 33, 869-871.	0.6	1
28	Transformation of graphene flakes into carbon nanostructures byÎ³-irradiation. Materials Research Express, 2017, 4, 045602.	1.6	1
29	The effect of structure on the low-temperature electrical conductivity of carbon nanocomposite temperature sensors. Low Temperature Physics, 2019, 45, 1104-1108.	0.6	1
30	Resistive switching effect in the n-InGaAs/GaAs heterostructures with double tunnel-coupled quantum wells. Low Temperature Physics, 2022, 48, 157-160.	0.6	1
31	Transient processes in electric transport in the powder MoS2 samples. Journal of Applied Physics, 2022, 131, .	2.5	1
32	<title>Resonant intersubband transitions of holes in uniaxially stressed p-Ge</title>. , 2001, , .		0
33	Negative residual infrared photoconduction in the p-SiGe/Si heterostructures with selectively doped quantum wells. Journal of Applied Physics, 2012, 112, 083715.	2.5	0
34	Terahertz emission and reflection associated with surface plasmon polaritons in n-GaN microstructures. , 2014, , .		0